

Photodetector, especially a photodiode array useful for optical data storage and transmission, image processing, pattern recognition and spectrometry, is produced by back face bonding of a thinned photodetector wafer to a contact substrate

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Abstract of DE19838442

A photodetector production process, comprising back face bonding of a supported thinned photodetector wafer to a contact substrate having conductor lines and connection pads, is new. A photodetector production process comprises: (a) producing a substrate wafer (1) with a photosensitive region between two laterally spaced conductive regions (4, 5) on its front face; (b) bonding the wafer front face to an auxiliary support; (c) thinning the wafer back face down to (near) the conductive regions; (d) preparing a contact substrate having one or more contacting levels with conductor lines and connection areas for contacting the conductive regions (4, 5); (e) bonding the thinned wafer back face to the contact substrate such that the conductive regions lie above the connection areas; (f) removing the auxiliary support; and (g) producing electrical connections between the connection areas and the conductive regions.

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